

ABSTRACT

5 The present invention provide a ceramic substrate for semiconductor manufacture and/or inspection which is conducive to decrease in α -rays radiated, and change of thermal conductivity with passage of the time, and which is superior in the temperature controllability.

10 This invention is related to a ceramic substrate for apparatuses for use in semiconductor manufacture and/or inspection,

wherein the level of α -rays radiated from said ceramic substrate exceeds $0.25 \text{ c/cm}^2 \cdot \text{hr}$ and is not higher than $50 \text{ c/cm}^2 \cdot \text{hr}$.